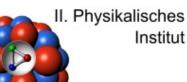


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d a рапда

Updates on the MVD-Strip-Detector







Entries 223212

80

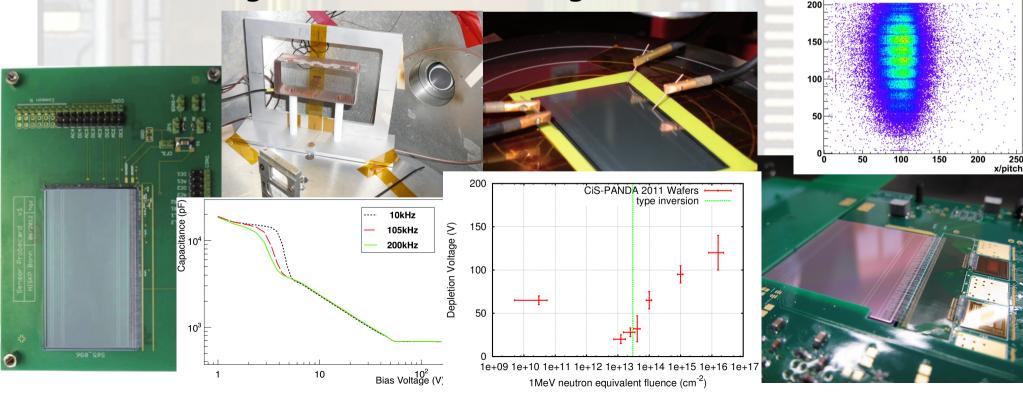
60

Detector Development

barrel sensors been intensively tested

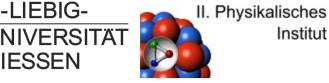
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- new engineering run submitted beginning 2013
 - → investigate different biasing method





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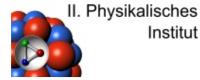


Detector Development

- disk sensors engineering run arrived @Jülich
- CiS Erfurt, same technology as barrel sensors

strip implants:	512 p ⁺ -strips in n-substrat and 512 n ⁺ -strips for the backside.	36.87	
Strip orientation:	parallel to the long sensor edges, skew angle = 15°	Stereo angle	
pitch:	67.5 μm	1001	
Biasing:	punch-through	19.94	
n-side charge sep:	p-spray	21.69	
height:	57.67 mm	21.69	
thickness:	250 – 300 µm		MVD group Jülich



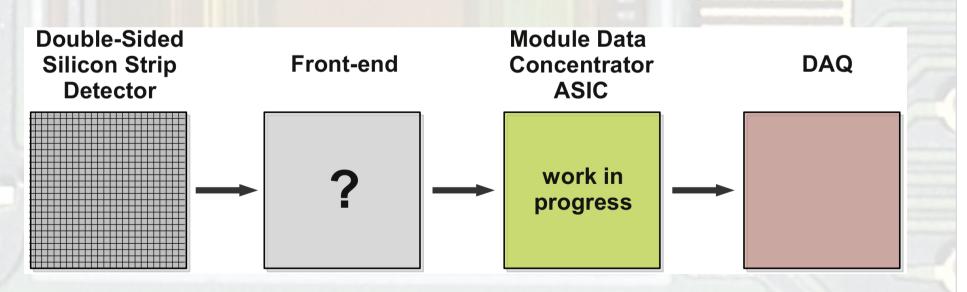


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Front-end Status

- decision for the strip detector front-end made
- based on TOFPET ASIC (EndoTOFPET-US coll.)
- modifications towards silicon strip detectors already started at INFN Torino





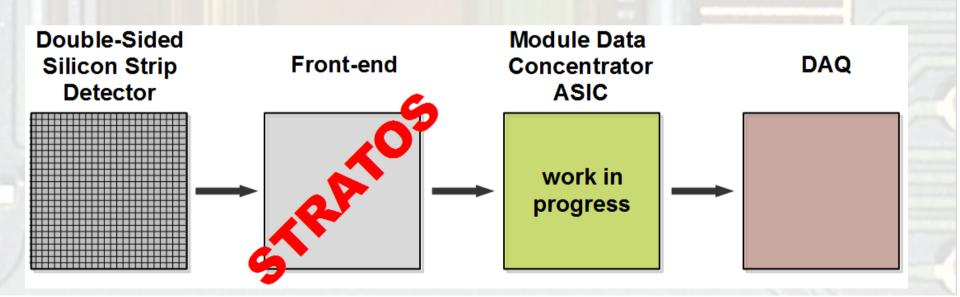


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Front-end Status

- decision for the strip detector front-end made
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MVD group Turin

Front-end Features

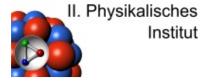
self-triggering, fully digital data output

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- analog part customized to sensor capacitance
- short ToT to avoid pile-up
- fast sampling (binning ~100ps)
 - using TDCs based on time interpolation
- high digitization resolution
 - clustering to improve spacial resolution
 - energy loss information as additional PID input



FSSEN



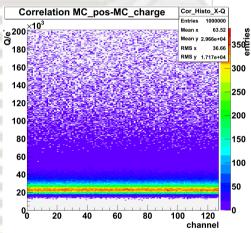


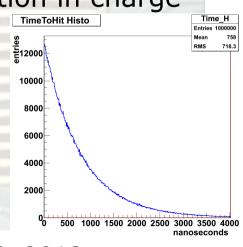
Strip Front-end Simulation

 fast and flexible using C++ and Root to compare with VHDL simulations

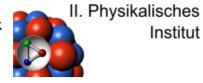
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- Features (so far):
 - adjustable number of channels (64 vs. 128)
 - adjustable sensor thickness (charge)
 - uniform distribution in position, landau distribution in charge
 - double strip hit with charge sharing (CoG)
 - exponential distribution in time
 - wave-form from device simulation
 - ... work in progress • **MVD** group Gießen









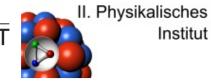
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MVD Strip-Detector count

	Barrel Part	Disk Part	Sum
Sensors	184 rectangular 64 square	48 trapezoidal	296
Front-ends	2536 (64 ch)	768 (64 ch)	3304
DC-DCs	1240	240	1480
MDCs	248	48	296





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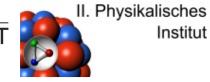


Gießen Infrastructure

- installed beginning of April
- size: 3,00 x 3,50 m², internal height: 2,20 m
- approx. 10m² clean room space
- designed for ISO 6
- measured to comply better then ISO 6







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Gießen Infrastructure



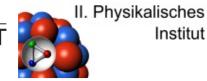
bonding machine: F&K Delvotec 5630 already in Gießen will be assembled soon





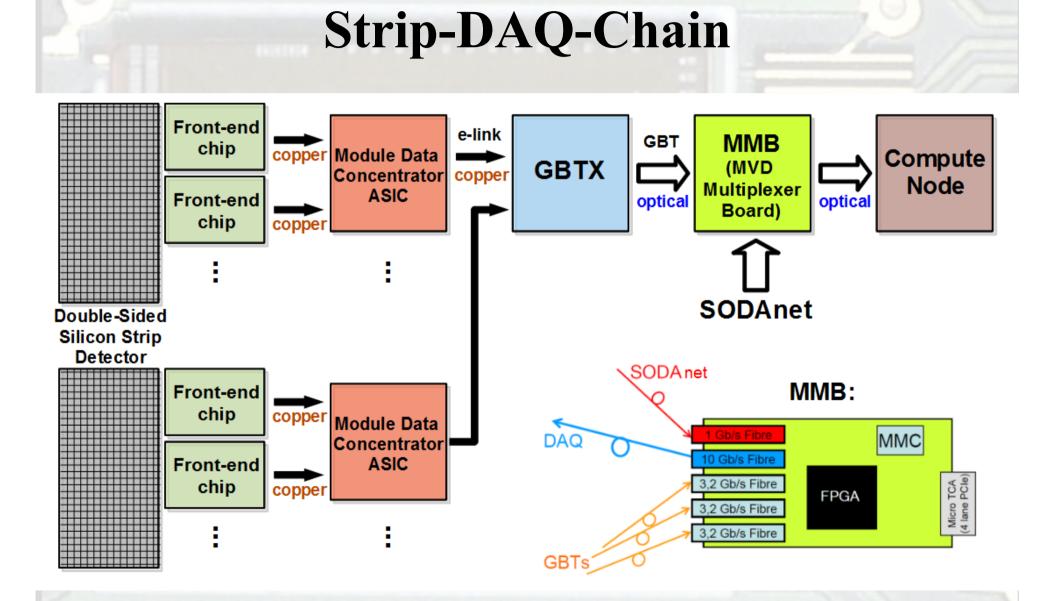
wafer prober: Cascade Microtech PA200BlueRay ordered





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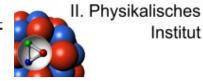


Module Data Concentrator

- all front-ends of one strip sensor connected to one module data concentrator ASIC (MDC)
- front-end data:
 - strip address
 - time information
 - ToT
- e-links (GBT) will be used for data transfer and slow control

H. Sohlbach, FH Iserlohn

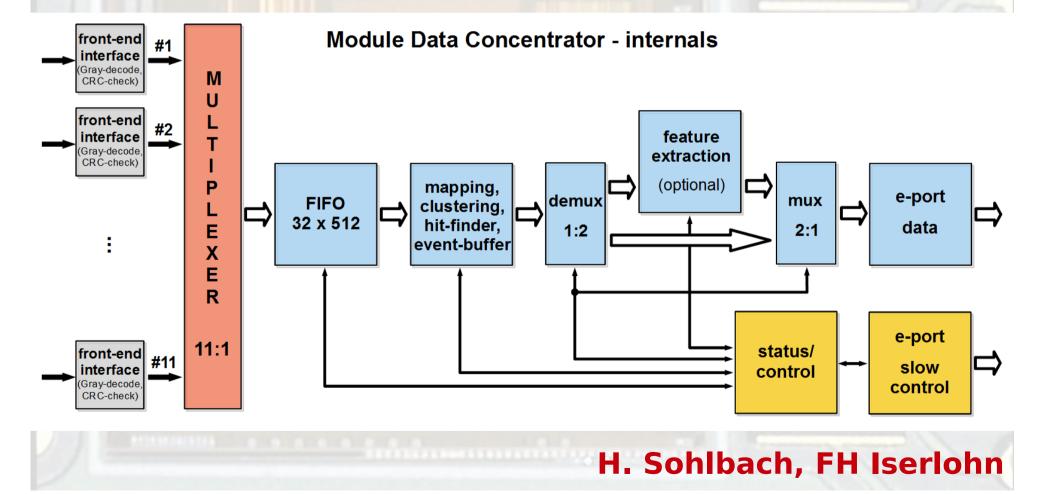




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Module Data Concentrator







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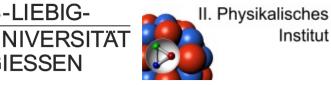
Module Data Concentrator

- Status as of April 2013
 - design versions: with/without feature extraction
 - design & simulation of FPGA prototype (VHDL-based) finished for:
 - 11:1 multiplexer, FIFO, clustering/hit finding
 - in design/redesigning: triple redundancy, clustering/hit finding, e-link, status/control
 - work on the specification of the front-end/module controller interface in progress

H. Sohlbach, FH Iserlohn



FSSFN





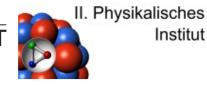
Summary

strip front-end in development

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- MDC in development
 - => both developed for the specific requirements of the PANDA MVD
 - feature set customized to our requirements
 - no dependence on external developments









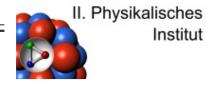
Thank you for your attention

STRATOS = **ST**rip **R**eadout **A**SIC **TO**rino **S**olution (Lancia Stratos)

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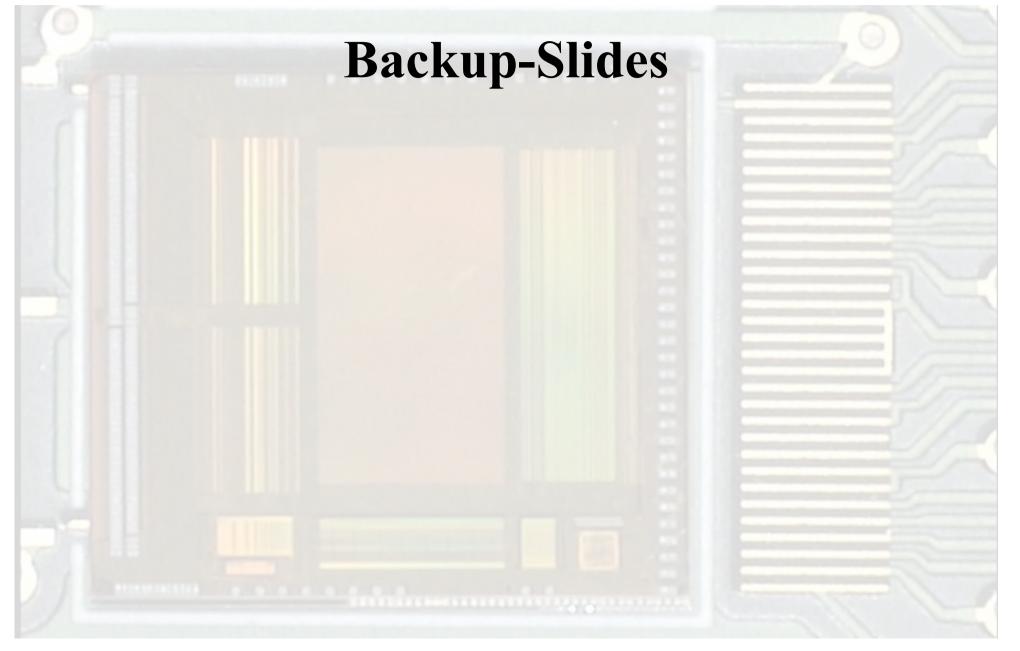






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Pile-up

 $\boldsymbol{P}_{pile-up} = 1 - e^{(-\dot{N}_{chn} \cdot \boldsymbol{t}_{ToT})}$ short ToT to avoid pile-up:

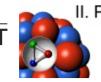
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assuming 36ns ToT (5fC ~ 1 MIP in a single strip): P(pile-up) = 0.036%@ 10kHz channel hit rate (SF=1) P(pile-up) = 0.072%@ 20kHz channel hit rate (SF=2) @ 40kHz channel hit rate (SF=4) P(pile-up) = 0.144%

assuming 60ns ToT (10fC ~ 2 MIP in a single strip): P(pile-up) = 0.06%@ 10kHz channel hit rate (SF=1) P(pile-up) = 0.12%@ 20kHz channel hit rate (SF=2) P(pile-up) = 0.24%@ 40kHz channel hit rate (SF=4)

(ToT based on device simulation from Valentino)





II. Physikalisches Institut



Gießen Infrastructure

